

Ming-Yang Li

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

11
papers

1,315
citations

9
h-index

13
g-index

13
ext. papers

1,588
ext. citations

17.9
avg. IF

4.09
L-index

#	Paper	IF	Citations
11	Capturing 3D atomic defects and phonon localization at the 2D heterostructure interface. <i>Science Advances</i> , 2021 , 7, eabi6699	14.3	2
10	Point Defects and Localized Excitons in 2D WSe. <i>ACS Nano</i> , 2019 , 13, 6050-6059	16.7	76
9	Demonstration of 40-nm Channel Length Top-Gate p-MOSFET of WS ₂ Channel Directly Grown on SiO ₂ /Si Substrates Using Area-Selective CVD Technology. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 5381-5386	2.9	3
8	Nanoscale Surface Photovoltage Mapping of 2D Materials and Heterostructures by Illuminated Kelvin Probe Force Microscopy. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 13564-13571	3.8	23
7	Observation of chiral phonons. <i>Science</i> , 2018 , 359, 579-582	33.3	110
6	Strain distributions and their influence on electronic structures of WSe-MoS laterally strained heterojunctions. <i>Nature Nanotechnology</i> , 2018 , 13, 152-158	28.7	135
5	Unraveling Spatially Heterogeneous Ultrafast Carrier Dynamics of Single-Layer WSe by Femtosecond Time-Resolved Photoemission Electron Microscopy. <i>Nano Letters</i> , 2018 , 18, 5172-5178	11.5	21
4	Single Atomically Sharp Lateral Monolayer p-n Heterojunction Solar Cells with Extraordinarily High Power Conversion Efficiency. <i>Advanced Materials</i> , 2017 , 29, 1701168	24	82
3	Atomic-Monolayer MoS Band-to-Band Tunneling Field-Effect Transistor. <i>Small</i> , 2016 , 12, 5676-5683	11	33
2	NANOELECTRONICS. Epitaxial growth of a monolayer WSe ₂ -MoS ₂ lateral p-n junction with an atomically sharp interface. <i>Science</i> , 2015 , 349, 524-8	33.3	811
1	TMD FinFET with 4 nm thin body and back gate control for future low power technology 2015 ,		18